## SILICON EPITAXIAL PLANAR SWITCHING DIODE

## Applications

- for switching circuits


Absolute Maximum Ratings ( $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$ )

| Parameter | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Peak Reverse Voltage | $\mathrm{V}_{\mathrm{RM}}$ | 80 | V |
| Reverse Voltage | $\mathrm{V}_{\mathrm{R}}$ | 80 | V |
| Forward Current | $\mathrm{I}_{\mathrm{F}}$ | 100 | mA |
| Peak Forward Current | $\mathrm{I}_{\mathrm{FM}}$ | 225 | mA |
| Non-repetitive Peak Forward Surge Current ( $\mathrm{t}=1 \mathrm{~s})$ | $\mathrm{I}_{\mathrm{FSM}}$ | 500 | mA |
| Junction Temperature | $\mathrm{T}_{J}$ | 150 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature Range | $\mathrm{T}_{\mathrm{s}}$ | -55 to +150 | ${ }^{\circ} \mathrm{C}$ |

Characteristics at $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$

| Parameter | Symbol | Min. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: |
| Forward Voltage <br> at $\mathrm{I}_{\mathrm{F}}=100 \mathrm{~mA}$ | $\mathrm{~V}_{\mathrm{F}}$ | - | 1.2 | V |
| Reverse Current <br> at $\mathrm{V}_{\mathrm{R}}=75 \mathrm{~V}$ | $\mathrm{I}_{\mathrm{R}}$ | - | 0.1 | $\mu \mathrm{~A}$ |
| Reverse Voltage <br> at $\mathrm{I}_{\mathrm{R}}=100 \mu \mathrm{~A}$ | $\mathrm{~V}_{\mathrm{R}}$ | 80 | - | V |
| Terminal Capacitance <br> at $\mathrm{V}_{\mathrm{R}}=0, \mathrm{f}=1 \mathrm{MHz}$ | $\mathrm{C}_{\mathrm{t}}$ | - | 15 | pF |
| Reverse Recovery Time <br> at $\mathrm{I}_{\mathrm{F}}=10 \mathrm{~mA}, \mathrm{~V}_{\mathrm{R}}=6 \mathrm{~V}, \mathrm{I}_{\mathrm{Ir}}=0.1 \cdot \mathrm{I}_{\mathrm{R}}, \mathrm{R}_{\mathrm{L}}=100 \Omega$ | $\mathrm{t}_{\mathrm{rr}}$ | - | 10 | ns |







(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)

MOODY


